

P-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY

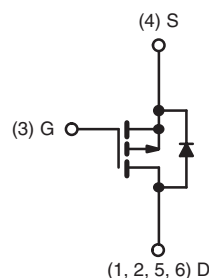
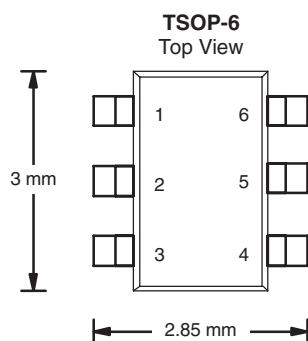
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
- 60	0.220 at $V_{GS} = - 10$ V	± 2.2
	0.310 at $V_{GS} = - 4.5$ V	± 1.9

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE
Available



Ordering Information: Si3459DV-T1-E3 (Lead (Pb)-free)
Si3459DV-T1-GE3 (Lead (Pb)-free and Halogen-free)

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	- 60	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 150$ °C) ^{a, b}	I_D	± 2.2	A
		± 1.7	
Pulsed Drain Current	I_{DM}	± 10	
Single Avalanche Current ($L = 0.1$ mH)	I_{AS}	- 7	
Maximum Power Dissipation ^b	P_D	2	W
		1.3	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	R_{thJA}		62.5	°C/W
		106		
Maximum Junction-to-Lead	R_{thJL}	35		

Notes:

a. Surface Mounted on FR4 board.

b. $t \leq 5$ s.

SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = -250\text{ }\mu\text{A}$	- 60			V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250\text{ }\mu\text{A}$	- 1			
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -60\text{ V}$, $V_{GS} = 0\text{ V}$			- 1	μA
		$V_{DS} = -60\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 150\text{ }^{\circ}\text{C}$			- 50	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = -5\text{ V}$, $V_{GS} = -10\text{ V}$	- 10			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -10\text{ V}$, $I_D = -2.2\text{ A}$		0.190	0.220	Ω
		$V_{GS} = -4.5\text{ V}$, $I_D = -1.9\text{ A}$		0.265	0.310	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -4.5\text{ V}$, $I_D = -2.2\text{ A}$		4		S
Dynamic ^b						
Total Gate Charge	Q_g	$V_{DS} = -30\text{ V}$, $V_{GS} = -10\text{ V}$, $I_D = -2.2\text{ A}$		7	14	nC
Gate-Source Charge	Q_{gs}			1.6		
Gate-Drain Charge	Q_{gd}			1.2		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -30\text{ V}$, $R_L = 30\text{ }\Omega$ $I_D \equiv -1\text{ A}$, $V_{GEN} = -10\text{ V}$, $R_g = 6\text{ }\Omega$		8	16	ns
Rise Time	t_r			12	24	
Turn-Off DelayTime	$t_{d(off)}$			23	45	
Fall Time	t_f			12	25	
Source-Drain Rating Characteristics ^b						
Continuous Current	I_S				- 1.7	A
Pulsed Current	I_{SM}				- 10	
Diode Forward Voltage ^a	V_{SD}	$I_S = -1.7\text{ A}$, $V_{GS} = 0\text{ V}$		- 0.8	- 1.2	V
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = -1.7\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$		50	90	ns

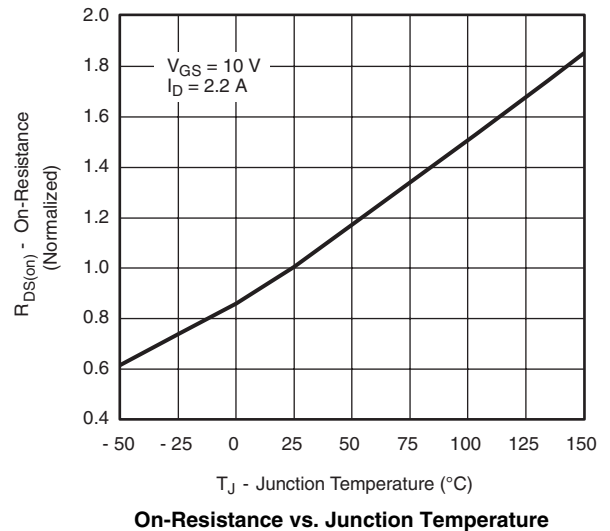
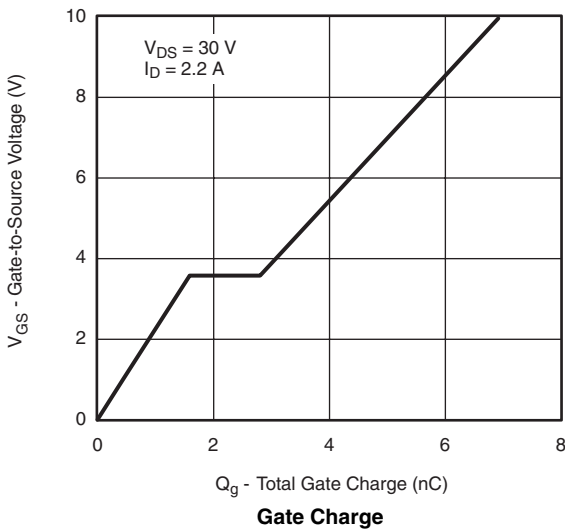
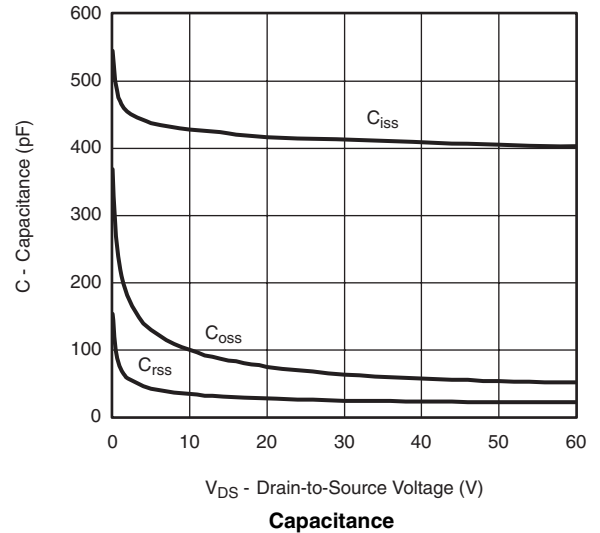
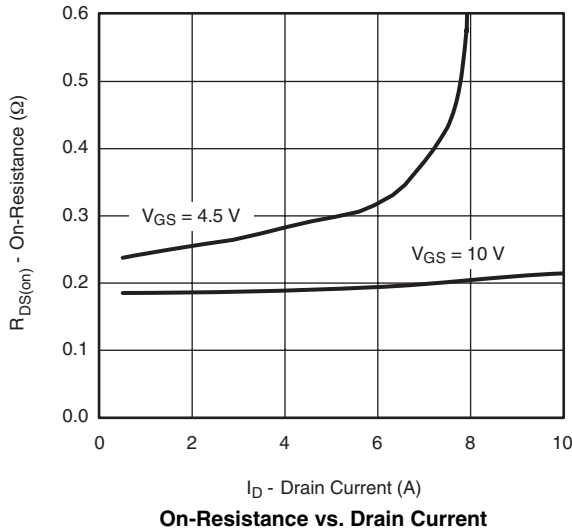
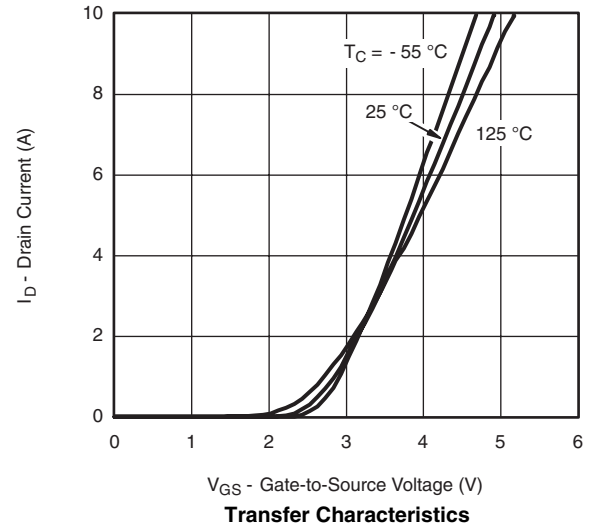
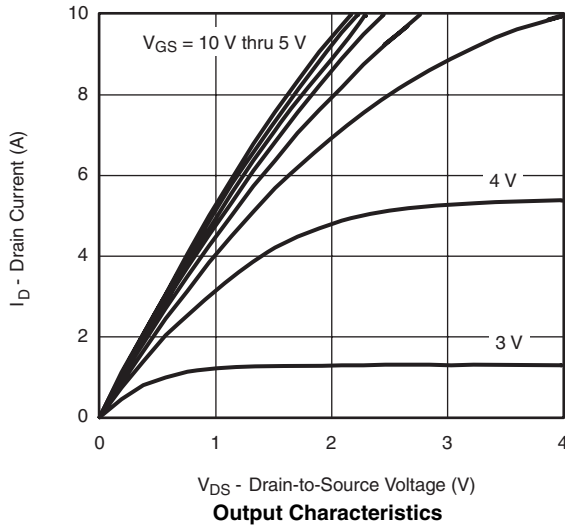
Notes:

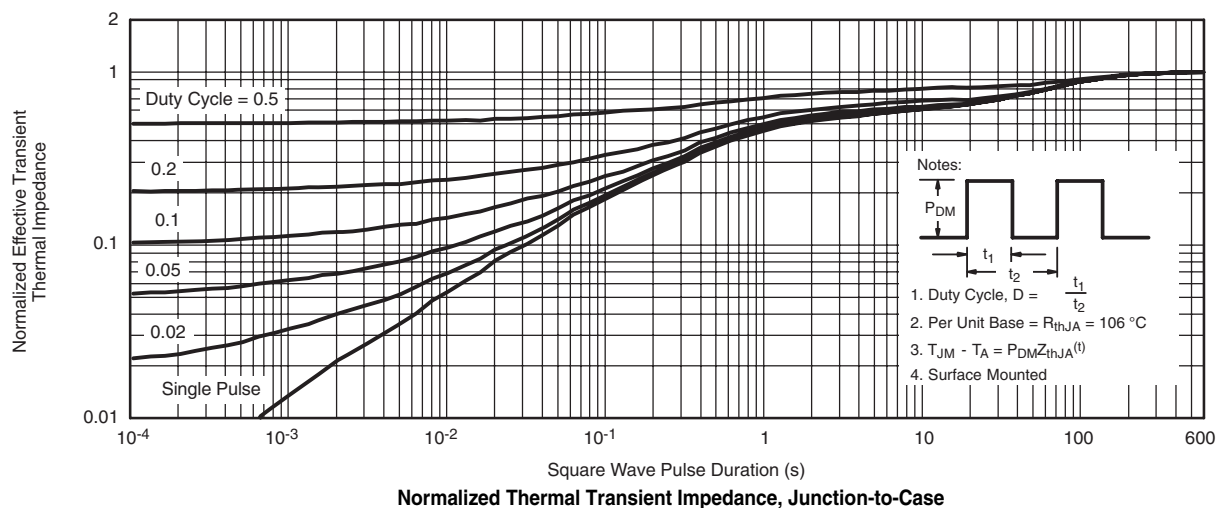
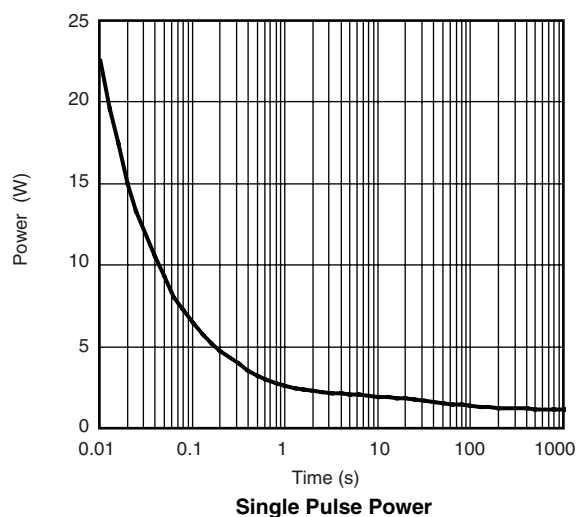
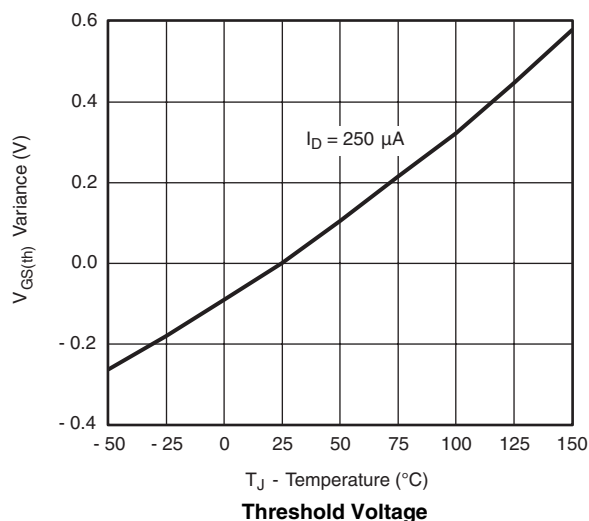
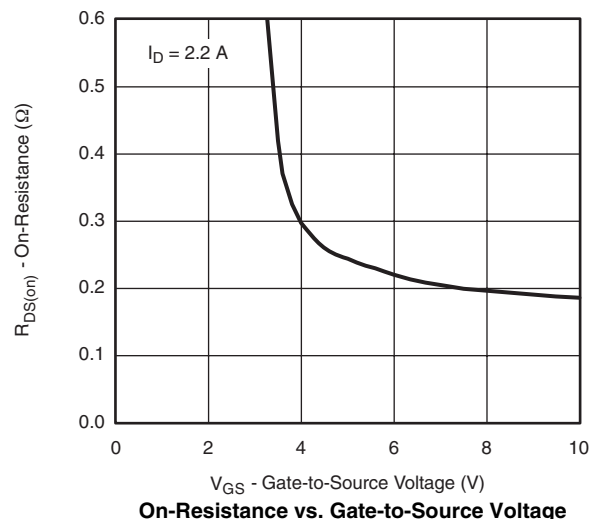
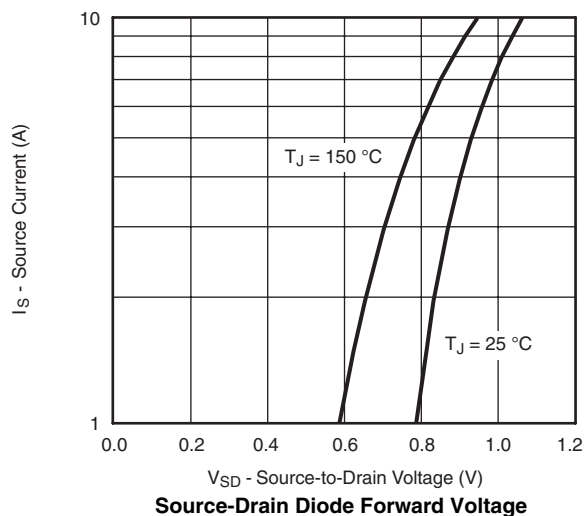
a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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